

METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE AND DEVELOPMENT APPARATUS

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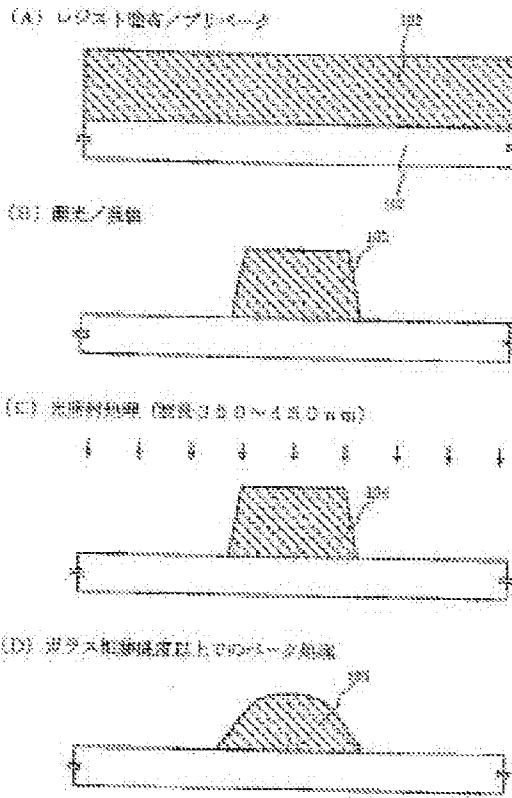
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Abstract of JP 2004006788 (A)

PROBLEM TO BE SOLVED: To provide a method for manufacturing a semiconductor device which ensures process margin in respect of a resist removing property, and achieves a balance between the formation of resist patterns each having a desired wall angle and the removing property of the resist pattern. ; **SOLUTION:** The method comprises processes for; forming the resist patterns each consisting of a positive resist comprising photosensitive materials; irradiating light, which is within a photosensitive wavelength of a photosensitizer, to the resist patterns; and baking the resist patterns at a temperature exceeding the glass-transition temperature. ; **COPYRIGHT:** (C) 2004,JPO



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(54) 【発明の名称】半導体装置の作製方法及び現像装置

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